

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S17	1721	257/355.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 02:46
S18	675	257/356.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 04:05
S19	865	257/360.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 04:31
S20	410	257/346.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 14:58
S21	82	semiconductor and (ESD or protection or overvoltage) and (triple near2 well) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:02
S22	5647	semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:03
S23	1402	semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:15
S24	1241	semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (source or drain or cmos or mosfet or fet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:04

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S25	397	semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (source or drain or cmos or mosfet or fet) and (substrate with resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:05
S26	442	semiconductor and (ESD or protection or overvoltage) and (wells) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408") and (substrate near4 contact) and (substrate with resistance)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:15
S27	417	semiconductor and (ESD or protection or overvoltage) and (wells same (substrate near4 contact)) and (NBL or buried) and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 05:15
S28	570	257/E27.067.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 15:23
S29	308	257/E29.064.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 15:41
S30	2990	257/E29.255.ccls. and (@ad<"20040408" or @rlad<"20040408")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 15:42
S31	413	257/E29.255.ccls. and (@ad<"20040408" or @rlad<"20040408") and (substrate with contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 15:42